10/774496

## THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Yoshihisa IBA

Patent No.: 7,196,003

Issued: March 27, 2007

For: METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

Attorney Docket Number: 042075

Customer Number: 38834

## REQUEST FOR CERTIFICATE OF CORRECTION

Mail Stop: COC

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

January 10, 2008

Sir:

The undersigned requests that a Certificate of Correction be issued for the above-identified patent as indicated on the attached Form PTO-1050.

This request is being made in order to correct Claims. Please delete the paragraphs beginning at column 6, line 64 and column 7, line 1, and insert the paragraph presented on Form PTO-1050. (See Amendment under 37 C.F.R. §1.111 filed on September 5, 2006). It is respectfully submitted that no new matter has been added.

Because this error is a Patent and Trademark Office printing error, it is respectfully submitted that no fee is required.

If any fees are required in connection with this paper, please charge Deposit Account No. 50-2866.

Respectfully submitted,

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Enclosures: Form PTO-1050

Certificate

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of Correction

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## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.: 7,196,003

DATED: March 27, 2007

INVENTOR(S): Yoshihisa IBA

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

## **On Claims**

Please delete the paragraphs beginning at column 6, line 64 and column 7, line 1, and insert the following paragraph (See Amendment under 37 C.F.R. &1.11 filed on September 5, 2006).

--The etching of SiO<sub>2</sub> film 6 is performed using the plasma etching device, for example, under the condition of 20 sccm of C4F6, 15 sccm of O2, 200 sccm of Ar, 4.00 Pa (30 mTorr) of pressure, and 1500 W of RF source power.

MAILING ADDRESS OF SENDER: Westerman, Hattori, Daniels & Adrian, LLP 1250 Connecticut Avenue NW - Suite 700 Washington, DC 20036-2657

PATENT NO. 7,196,003

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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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